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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	8MHz
Connectivity	SCI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	39
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	0°C ~ 70°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08rc8fge

MC9S08RG60 Data Sheet

Covers: MC9S08RC8/16/32/60
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MC9S08RG60/D
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List of Chapters

Chapter 1
Introduction

1.1 Overview

The MC9S08RC/RD/RE/RG are members of the low-cost, high-performance HCS08 Family of 8-bit microcontroller units (MCUs). All MCUs in this family use the enhanced HCS08 core and are available with a variety of modules, memory sizes, memory types, and package types.

1.2 Features

Features of the MC9S08RC/RD/RE/RG Family of devices are listed here. Please see Table 1-1 for the features that are available on the different family members.

HCS08 CPU (Central Processor Unit)	• Object code fully upward-compatible with M68HC05 and M68HC08 Families • HC08 instruction set with added BGND instruction • Support for up to 32 interrupt/reset sources • Power-saving modes: wait plus three stops
On-Chip Memory	• On-chip in-circuit programmable FLASH memory with block protection and security option • On-chip random-access memory (RAM)
Oscillator (OSC)	• Low power oscillator capable of operating from crystal or resonator from 1 to 16 MHz • 8 MHz internal bus frequency
Analog Comparator (ACMP1)	• On-chip analog comparator with internal reference (ACMP1) • Full rail-to-rail supply operation • Option to compare to a fixed internal bandgap reference voltage
Serial Communications Interface Module (SCI1)	• Full-duplex, standard non-return-to-zero (NRZ) format • Double-buffered transmitter and receiver with separate enables • Programmable 8-bit or 9-bit character length • Programmable baud rates (13-bit modulo divider)
Serial Peripheral Interface Module (SPI1)	• Master or slave mode operation • Full-duplex or single-wire bidirectional option • Programmable transmit bit rate • Double-buffered transmit and receive • Serial clock phase and polarity options • Slave select output • Selectable MSB-first or LSB-first shifting

Table 4-2. High-Page Register Summary (continued)

Address	Register Name	Bit 7	6	5	4	3	2	1	Bit 0
$1809	SPMSC1	LVDF	LVDACK	LVDIE	SAFE	LVDRE	—	—	—
$180A	SPMSC2	LVWF	LVWACK	0	0	PPDF	PPDACK	PDC	PPDC
$180B–$180F	Reserved	— —	— —	— —	— —	— —	— —	— —	— —
$1810	DBGCAH	Bit 15	14	13	12	11	10	9	Bit 8
$1811	DBGCAL	Bit 7	6	5	4	3	2	1	Bit 0
$1812	DBGCBH	Bit 15	14	13	12	11	10	9	Bit 8
$1813	DBGCBL	Bit 7	6	5	4	3	2	1	Bit 0
$1814	DBGFH	Bit 15	14	13	12	11	10	9	Bit 8
$1815	DBGFL	Bit 7	6	5	4	3	2	1	Bit 0
$1816	DBGC	DBGEN	ARM	TAG	BRKEN	RWA	RWAEN	RWB	RWBEN
$1817	DBGT	TRGSEL	BEGIN	0	0	TRG3	TRG2	TRG1	TRG0
$1818	DBGS	AF	BF	ARMF	0	CNT3	CNT2	CNT1	CNT0
$1819–$181F	Reserved	— —	— —	— —	— —	— —	— —	— —	— —
$1820	FCDIV	DIVLD	PRDIV8	DIV5	DIV4	DIV3	DIV2	DIV1	DIV0
$1821	FOPT	KEYEN	FNORED	0	0	0	0	SEC01	SEC00
$1822	Reserved	—	—	—	—	—	—	—	—
$1823	FCNFG	0	0	KEYACC	0	0	0	0	0
$1824	FPROT	FPOPEN	FPDIS	FPS2	FPS1	FPS0	0	0	0
$1825	FSTAT	FCBEF	FCCF	FPVIOL	FACCERR	0	FBLANK	0	0
$1826	FCMD	FCMD7	FCMD6	FCMD5	FCMD4	FCMD3	FCMD2	FCMD1	FCMD0
$1827–$182B	Reserved	— —	— —	— —	— —	— —	— —	— —	— —

1. The ILAD bit is only present on 16K and 8K versions of the devices.

Nonvolatile FLASH registers, shown in Table 4-3, are located in the FLASH memory. These registers include an 8-byte backdoor key that optionally can be used to gain access to secure memory resources. During reset events, the contents of NVPROT and NVOPT in the nonvolatile register area of the FLASH memory are transferred into corresponding FPROT and FOPT working registers in the high-page registers to control security and block protection options.

Table 4-3. Nonvolatile Register Summary

Address	Register Name	Bit 7	6	5	4	3	2	1	Bit 0
$FFB0–$FFB7	NVBACKKEY	8-Byte Comparison Key							
$FFB8–$FFBC	Reserved	— —	— —	— —	— —	— —	— —	— —	— —
$FFBD	NVPROT	FPOPEN	FPDIS	FPS2	FPS1	FPS0	0	0	0
$FFBE	Reserved	—	—	—	—	—	—	—	—
$FFBF	NVOPT	KEYEN	FNORED	0	0	0	0	SEC01	SEC00

4.4.1 Features

Features of the FLASH memory include:

- FLASH Size
  - MC9S08RC/RD/RE/RG60 — 63374 bytes (124 pages of 512 bytes each)
  - MC9S08RC/RD/RE/RG32 — 32768 bytes (64 pages of 512 bytes each)
  - MC9S08RC/RD/RE16 — 16384 bytes (32 pages of 512 bytes each)
  - MC9S08RC/RD/RE8 — 8192 bytes (16 pages of 512 bytes each)
- Single power supply program and erase
- Command interface for fast program and erase operation
- Up to 100,000 program/erase cycles at typical voltage and temperature
- Flexible block protection
- Security feature for FLASH and RAM
- Auto power-down for low-frequency read accesses

4.4.2 Program and Erase Times

Before any program or erase command can be accepted, the FLASH clock divider register (FCDIV) must be written to set the internal clock for the FLASH module to a frequency (f_{FCLK}) between 150 kHz and 200 kHz (see Section 4.6.1, "FLASH Clock Divider Register (FCDIV)"). This register can be written only once, so normally this write is done during reset initialization. FCDIV cannot be written if the access error flag, FACCERR in FSTAT, is set. The user must ensure that FACCERR is not set before writing to the FCDIV register. One period of the resulting clock ($1/f_{FCLK}$) is used by the command processor to time program and erase pulses. An integer number of these timing pulses are used by the command processor to complete a program or erase command.

Table 4-4 shows program and erase times. The bus clock frequency and FCDIV determine the frequency of FCLK (f_{FCLK}). The time for one cycle of FCLK is $t_{FCLK} = 1/f_{FCLK}$. The times are shown as a number of cycles of FCLK and as an absolute time for the case where $t_{FCLK} = 5$ µs. Program and erase times shown include overhead for the command state machine and enabling and disabling of program and erase voltages.

Table 4-4. Program and Erase Times

Parameter	Cycles of FCLK	Time if FCLK = 200 kHz
Byte program	9	45 µs
Byte program (burst)	4	20 µs[1]
Page erase	4000	20 ms
Mass erase	20,000	100 ms

1. Excluding start/end overhead

program time provided that the conditions above are met. In the case where the next sequential address is the beginning of a new row, the program time for that byte will be the standard time instead of the burst time. This is because the high voltage to the array must be disabled and then enabled again. If a new burst command has not been queued before the current command completes, then the charge pump will be disabled and high voltage removed from the array.

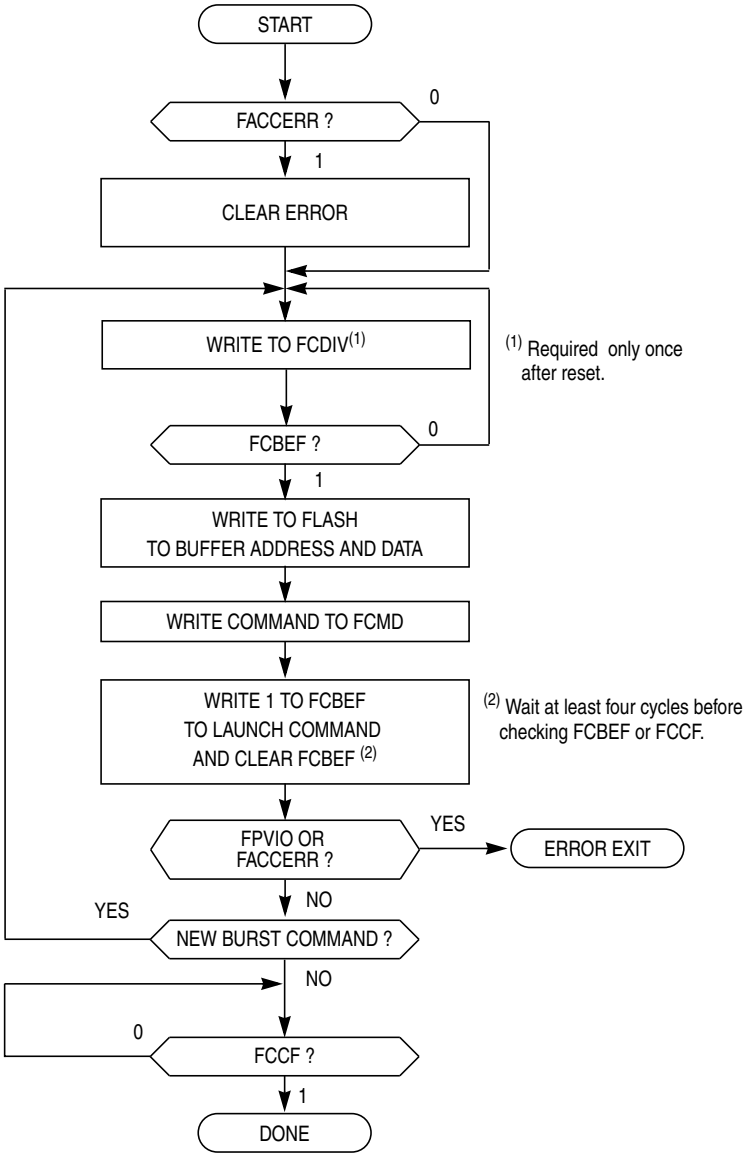


Figure 4-4. FLASH Burst Program Flowchart

4.4.5 Access Errors

An access error occurs whenever the command execution protocol is violated.

Any of the following specific actions will cause the access error flag (FACCERR) in FSTAT to be set. FACCERR must be cleared by writing a 1 to FACCERR in FSTAT before any command can be processed:

- Writing to a FLASH address before the internal FLASH clock frequency has been set by writing to the FCDIV register
- Writing to a FLASH address while FCBEF is not set (A new command cannot be started until the command buffer is empty.)
- Writing a second time to a FLASH address before launching the previous command (There is only one write to FLASH for every command.)
- Writing a second time to FCMD before launching the previous command (There is only one write to FCMD for every command.)
- Writing to any FLASH control register other than FCMD after writing to a FLASH address
- Writing any command code other than the five allowed codes ($05, $20, $25, $40, or $41) to FCMD
- Accessing (read or write) any FLASH control register other than the write to FSTAT (to clear FCBEF and launch the command) after writing the command to FCMD
- The MCU enters stop mode while a program or erase command is in progress (The command is aborted.)
- Writing the byte program, burst program, or page erase command code ($20, $25, or $40) with a background debug command while the MCU is secured (The background debug controller can only do blank check and mass erase commands when the MCU is secure.)
- Writing 0 to FCBEF to cancel a partial command

4.4.6 FLASH Block Protection

Block protection prevents program or erase changes for FLASH memory locations in a designated address range. Mass erase is disabled when any block of FLASH is protected. The MC9S08RC/RD/RE/RG allows a block of memory at the end of FLASH, and/or the entire FLASH memory to be block protected. A disable control bit and a 3-bit control field, for each of the blocks, allows the user to independently set the size of these blocks. A separate control bit allows block protection of the entire FLASH memory array. All seven of these control bits are located in the FPROT register (see Section 4.6.4, “FLASH Protection Register (FPROT and NVPROT)“).

At reset, the high-page register (FPROT) is loaded with the contents of the NVPROT location that is in the nonvolatile register block of the FLASH memory. The value in FPROT cannot be changed directly from application software so a runaway program cannot alter the block protection settings. If the last 512 bytes of FLASH (which includes the NVPROT register) is protected, the application program cannot alter the block protection settings (intentionally or unintentionally). The FPROT control bits can be written by background debug commands to allow a way to erase a protected FLASH memory.

One use for block protection is to block protect an area of FLASH memory for a bootloader program. This bootloader program then can be used to erase the rest of the FLASH memory and reprogram it. Because the bootloader is protected, it remains intact even if MCU power is lost during an erase and reprogram operation.

2. Writing the user-entered key values to the NVBACKKEY through NVBACKKEY+7 locations. These writes must be done in order starting with the value for NVBACKKEY and ending with NVBACKKEY+7. STHX must not be used for these writes because these writes cannot be done on adjacent bus cycles. User software normally would get the key codes from outside the MCU system through a communication interface such as a serial I/O.
3. Writing 0 to KEYACC in the FCNFG register. If the 8-byte key that was just written matches the key stored in the FLASH locations, SEC01:SEC00 are automatically changed to 1:0 and security will be disengaged until the next reset.

The security key can be written only from RAM, so it cannot be entered through background commands without the cooperation of a secure user program. The FLASH memory cannot be accessed by read operations while KEYACC is set.

The backdoor comparison key (NVBACKKEY through NVBACKKEY+7) is located in FLASH memory locations in the nonvolatile register space so users can program these locations exactly as they would program any other FLASH memory location. The nonvolatile registers are in the same 512-byte block of FLASH as the reset and interrupt vectors, so block protecting that space also block protects the backdoor comparison key. Block protects cannot be changed from user application programs, so if the vector space is block protected, the backdoor security key mechanism cannot permanently change the block protect, security settings, or the backdoor key.

Security can always be disengaged through the background debug interface by performing these steps:

1. Disable any block protections by writing FPROT. FPROT can be written only with background debug commands, not from application software.
2. Mass erase FLASH if necessary.
3. Blank check FLASH. Provided FLASH is completely erased, security is disengaged until the next reset.

   To avoid returning to secure mode after the next reset, program NVOPT so SEC01:SEC00 = 1:0.

4.6 FLASH Registers and Control Bits

The FLASH module has nine 8-bit registers in the high-page register space, three locations in the nonvolatile register space in FLASH memory that are copied into three corresponding high-page control registers at reset. There is also an 8-byte comparison key in FLASH memory. Refer to Table 4-2 and Table 4-3 for the absolute address assignments for all FLASH registers. This section refers to registers and control bits only by their names. A Freescale-provided equate or header file normally is used to translate these names into the appropriate absolute addresses.

4.6.1 FLASH Clock Divider Register (FCDIV)

Bit 7 of this register is a read-only status flag. Bits 6 through 0 may be read at any time but can be written only one time. Before any erase or programming operations are possible, write to this register to set the frequency of the clock for the nonvolatile memory system within acceptable limits.

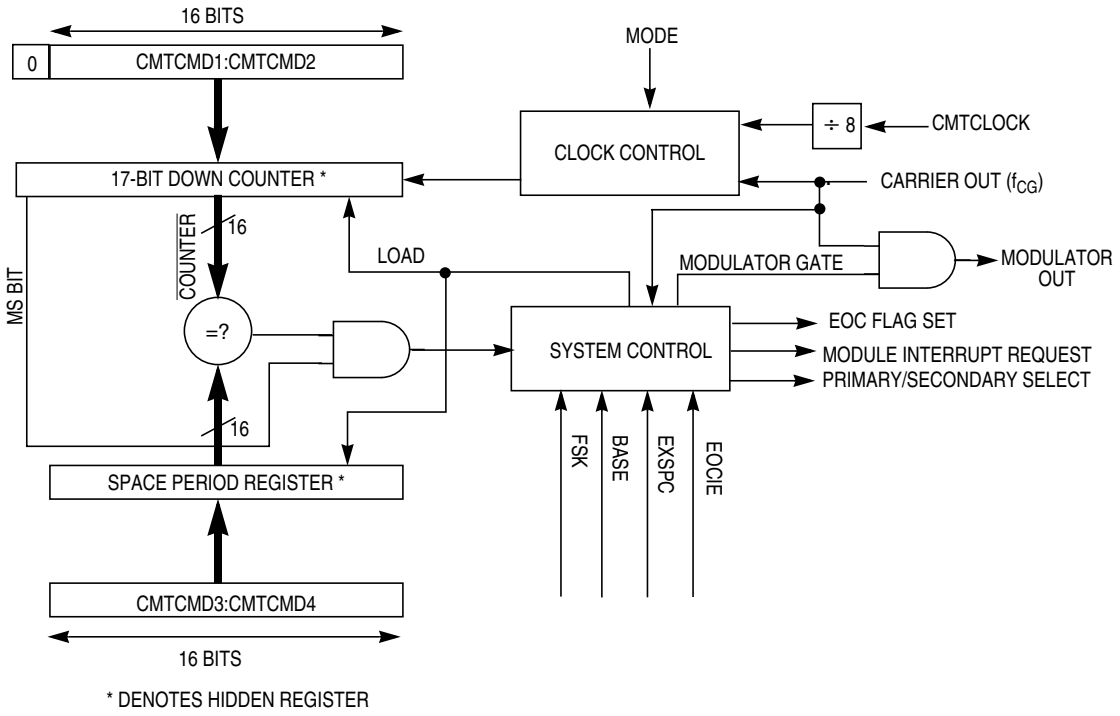


Figure 8-4. Modulator Block Diagram

8.5.2.1 Time Mode

When the modulator operates in time mode (MCGEN bit is set, BASE bit is clear, and FSK bit is clear), the modulation mark period consists of an integer number of CMTCLK ÷ 8 clock periods. The modulation space period consists of zero or an integer number of CMTCLK ÷ 8 clock periods. With an 8 MHz bus and CMTDIV1:CMTDIV0 = 00, the modulator resolution is 1 µs and has a maximum mark and space period of about 65.535 ms each. See Figure 8-5 for an example of the time mode and baseband mode outputs.

The mark and space time equations for time and baseband mode are:

$$t_{mark} = (CMTCMD1{:}CMTCMD2 + 1) \div (f_{CMTCLK} \div 8) \qquad \textit{Eqn. 8-5}$$

$$t_{space} = CMTCMD3{:}CMTCMD4 \div (f_{CMTCLK} \div 8) \qquad \textit{Eqn. 8-6}$$

where CMTCMD1:CMTCMD2 and CMTCMD3:CMTCMD4 are the decimal values of the concatenated registers.

NOTE

If the modulator is disabled while the t_{mark} time is less than the programmed carrier high time ($t_{mark} < CMTCGH1/f_{CMTCLK}$), the modulator can enter into an illegal state and end the curent cycle before the programmed value. Make sure to program t_{mark} greater than the carrier high time to avoid this illegal state.

The space period provides an interpulse gap (no carrier). If CMTCMD3:CMTCMD4 = $0000, then the modulator and carrier generator will switch between carrier frequencies without a gap or any carrier glitches (zero space).

Using timing data for carrier burst and interpulse gap length calculated by the CPU, FSK mode can automatically generate a phase-coherent, dual-frequency FSK signal with programmable burst and interburst gaps.

The mark and space time equations for FSK mode are:

$$t_{mark} = (CMTCMD1:CMTCMD2 + 1) \div f_{CG} \quad \textit{Eqn. 8-7}$$

$$t_{space} = CMTCMD3:CMTCMD4 \div f_{CG} \quad \textit{Eqn. 8-8}$$

Where f_{CG} is the frequency output from the carrier generator. The example in Figure 8-6 shows what the IRO pin output looks like in FSK mode with the following values: CMTCMD1:CMTCMD2 = $0003, CMTCMD3:CMTCMD4 = $0002, primary carrier high count = $01, primary carrier low count = $02, secondary carrier high count = $03, and secondary carrier low count = $01.

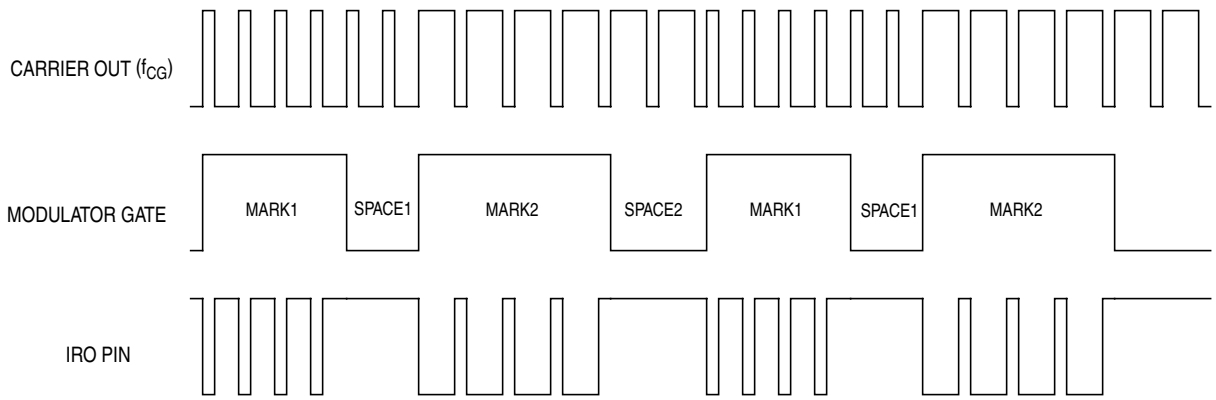


Figure 8-6. Example CMT Output in FSK Mode

8.5.3 Extended Space Operation

In time, baseband, or FSK mode, the space period can be made longer than the maximum possible value of the space period register. Setting the EXSPC bit in the CMTMSC register will force the modulator to treat the next modulation period (beginning with the next load of the counter and space period register) as a space period equal in length to the mark and space counts combined. Subsequent modulation periods will consist entirely of these extended space periods with no mark periods. Clearing EXSPC will return the modulator to standard operation at the beginning of the next modulation period.

8.5.3.1 EXSPC Operation in Time Mode

To calculate the length of an extended space in time or baseband modes, add the mark and space times and multiply by the number of modulation periods that EXSPC is set.

8.5.5 CMT Interrupts

The end of cycle flag (EOCF) is set when:

- The modulator is not currently active and the MCGEN bit is set to begin the initial CMT transmission
- At the end of each modulation cycle (when the counter is reloaded from CMTCMD1:CMTCMD2) while the MCGEN bit is set

In the case where the MCGEN bit is cleared and then set before the end of the modulation cycle, the EOCF bit will not be set when the MCGEN is set, but will become set at the end of the current modulation cycle.

When the MCGEN becomes disabled, the CMT module does not set the EOC flag at the end of the last modulation cycle.

The EOCF bit is cleared by reading the CMT modulator status and control register (CMTMSC) followed by an access of CMTCMD2 or CMTCMD4.

If the EOC interrupt enable (EOCIE) bit is high when the EOCF bit is set, the CMT module will generate an interrupt request. The EOCF bit must be cleared within the interrupt service routine to prevent another interrupt from being generated after exiting the interrupt service routine.

The EOC interrupt is coincident with loading the down-counter with the contents of CMTCMD1:CMTCMD2 and loading the space period register with the contents of CMTCMD3:CMTCMD4. The EOC interrupt provides a means for the user to reload new mark/space values into the modulator data registers. Modulator data register updates will take effect at the end of the current modulation cycle. Note that the down-counter and space period register are updated at the end of every modulation cycle, regardless of interrupt handling and the state of the EOCF flag.

8.5.6 Wait Mode Operation

During wait mode the CMT, if enabled, will continue to operate normally. However, there will be no new codes or changes of pattern mode while in wait mode, because the CPU is not operating.

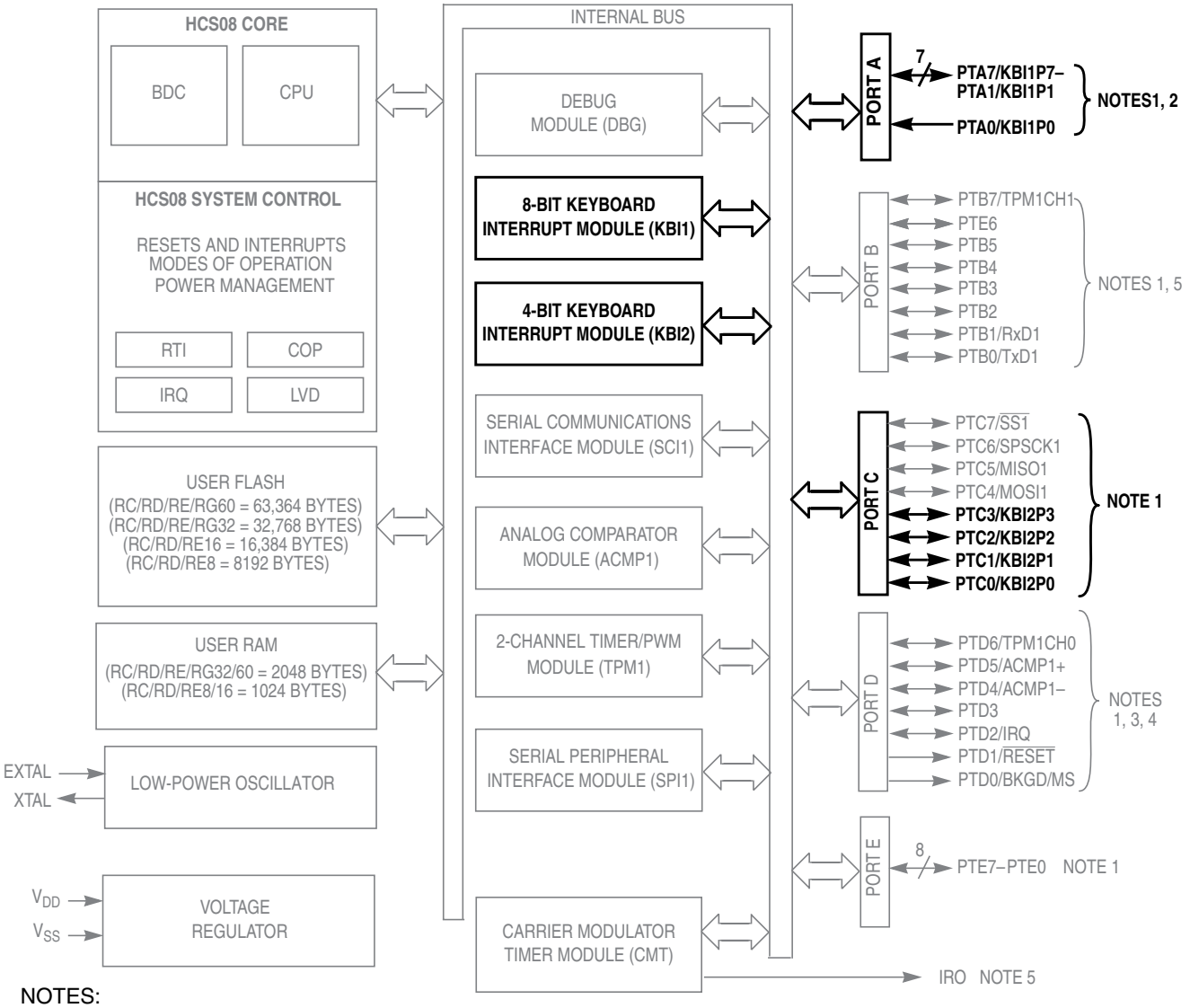
8.5.7 Stop Mode Operation

During all stop modes, clocks to the CMT module are halted.

In stop1 and stop2 modes, all CMT register data is lost and must be re-initialized upon recovery from these two stop modes.

No CMT module registers are affected in stop3 mode.

Note, because the clocks are halted, the CMT will resume upon exit from stop (only in stop3 mode). Software should ensure stop2 or stop3 mode is not entered while the modulator is in operation to prevent the IRO pin from being asserted while in stop mode. This may require a time-out period from the time that the MCGEN bit is cleared to allow the last modulator cycle to complete.



NOTES:

7. Port pins are software configurable with pullup device if input port
8. PTA0 does not have a clamp diode to V_{DD}. PTA0 should not be driven above V_{DD}. Also, PTA0 does not pullup to V_{DD} when internal pullup is enabled.
9. IRQ pin contains software configurable pullup/pulldown device if IRQ enabled (IRQPE = 1)
10. The RESET pin contains integrated pullup device enabled if reset enabled (RSTPE = 1)
11. High current drive
12. Pins PTA[7:4] contain both pullup and pulldown devices. Pulldown enabled when KBI is enabled (KBIPEn = 1) and rising edge is selected (KBEDGn = 1).

Figure 9-1. MC9S08RC/RD/RE/RG Block Diagram

12.3 Functional Description

The SCI allows full-duplex, asynchronous, NRZ serial communication among the MCU and remote devices, including other MCUs. The SCI comprises a baud rate generator, transmitter, and receiver block. The transmitter and receiver operate independently, although they use the same baud rate generator. During normal operation, the MCU monitors the status of the SCI, writes the data to be transmitted, and processes received data. The following describes each of the blocks of the SCI.

12.3.1 Baud Rate Generation

As shown in Figure 12-11, the clock source for the SCI baud rate generator is the bus-rate clock.

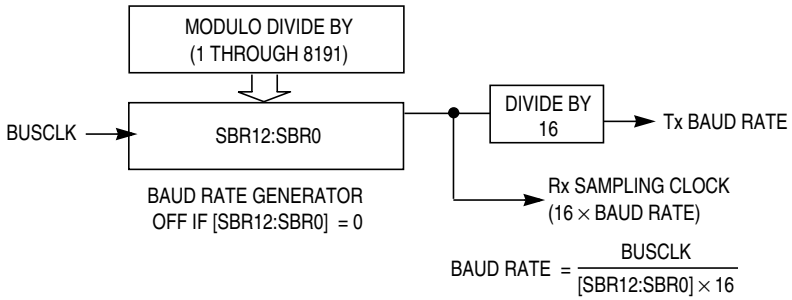


Figure 12-11. SCI Baud Rate Generation

SCI communications require the transmitter and receiver (which typically derive baud rates from independent clock sources) to use the same baud rate. Allowed tolerance on this baud frequency depends on the details of how the receiver synchronizes to the leading edge of the start bit and how bit sampling is performed.

The MCU resynchronizes to bit boundaries on every high-to-low transition, but in the worst case, there are no such transitions in the full 10- or 11-bit time character frame so any mismatch in baud rate is accumulated for the whole character time. For a Freescale Semiconductor SCI system whose bus frequency is driven by a crystal, the allowed baud rate mismatch is about ±4.5 percent for 8-bit data format and about ±4 percent for 9-bit data format. Although baud rate modulo divider settings do not always produce baud rates that exactly match standard rates, it is normally possible to get within a few percent, which is acceptable for reliable communications.

12.3.2 Transmitter Functional Description

This section describes the overall block diagram for the SCI transmitter (Figure 12-1), as well as specialized functions for sending break and idle characters.

The transmitter is enabled by setting the TE bit in SCI1C2. This queues a preamble character that is one full character frame of the idle state. The transmitter then remains idle until data is available in the transmit data buffer. Programs store data into the transmit data buffer by writing to the SCI data register (SCI1D).

The central element of the SCI transmitter is the transmit shift register that is either 10 or 11 bits long depending on the setting in the M control bit. For the remainder of this section, we will assume M = 0, selecting the normal 8-bit data mode. In 8-bit data mode, the shift register holds a start bit, eight data bits, and a stop bit. When the transmit shift register is available for a new SCI character, the value waiting in

Table 13-2. SPI Baud Rate Prescaler Divisor

SPPR2:SPPR1:SPPR0	Prescaler Divisor
0:0:0	1
0:0:1	2
0:1:0	3
0:1:1	4
1:0:0	5
1:0:1	6
1:1:0	7
1:1:1	8

SPR2:SPR1:SPR0 — SPI Baud Rate Divisor

This 3-bit field selects one of eight divisors for the SPI baud rate divider as shown in Figure 13-3. The input to this divider comes from the SPI baud rate prescaler (see Figure 13-4). The output of this divider is the SPI bit rate clock for master mode.

Table 13-3. SPI Baud Rate Divisor

SPR2:SPR1:SPR0	Rate Divisor
0:0:0	2
0:0:1	4
0:1:0	8
0:1:1	16
1:0:0	32
1:0:1	64
1:1:0	128
1:1:1	256

Figure 15-4 shows the host receiving a logic 0 from the target HCS08 MCU. Because the host is asynchronous to the target MCU, there is a 0-to-1 cycle delay from the host-generated falling edge on BKGD to the start of the bit time as perceived by the target MCU. The host initiates the bit time but the target HCS08 finishes it. Because the target wants the host to receive a logic 0, it drives the BKGD pin low for 13 BDC clock cycles, then briefly drives it high to speed up the rising edge. The host samples the bit level about 10 cycles after starting the bit time.

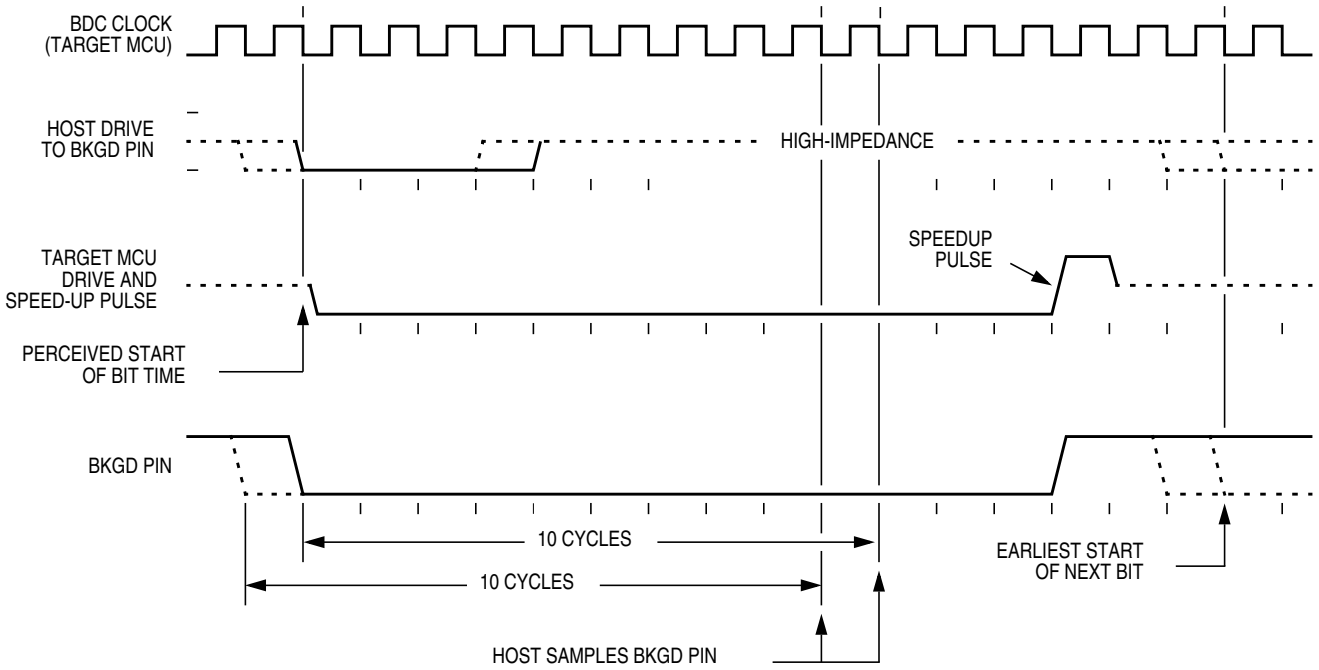


Figure 15-4. BDM Target-to-Host Serial Bit Timing (Logic 0)

A.6 Supply Current Characteristics

Table A-6. Supply Current Characteristics

Parameter	Symbol	V_{DD} (V)[1]	Typical[2]	Max	Temp. (°C)
Run supply current[3] measured at (CPU clock = 2 MHz, f_{Bus} = 1 MHz)	RI_{DD}	3	500 µA	1.525 mA 1.525 mA	70 85
		2	450 µA	1.475 mA 1.475 mA	70 85
Run supply current[3] measured at (CPU clock = 16 MHz, f_{Bus} = 8 MHz)	RI_{DD}	3	3.8 mA	4.8 mA 4.8 mA	70 85
		2	2.6 mA	3.6 mA 3.6 mA	70 85
Stop1 mode supply current	$S1I_{DD}$	3	100 nA	350 nA 736 nA	70 85
		2	100 nA	150 nA 450 nA	70 85
Stop2 mode supply current	$S2I_{DD}$	3	500 nA	1.20 µA 1.90 µA	70 85
		2	500 nA	1.00 µA 1.70 µA	70 85
Stop3 mode supply current	$S3I_{DD}$	3	600 nA	2.65 µA 4.65 µA	70 85
		2	500 nA	2.30 µA 4.30 µA	70 85
RTI adder from stop2 or stop3		3	300 nA		
		2	300 nA		
Adder for LVD reset enabled in stop3		3	70 µA		
		2	60 µA		

1. 3 V values are 100% tested; 2 V values are characterized but not tested.
2. Typicals are measured at 25°C.
3. Does not include any dc loads on port pins

A.7 Analog Comparator (ACMP) Electricals

Table A-7. ACMP Electrical Specifications (Temp Range = -40 to 85° C Ambient)

Characteristic	Symbol	Min	Typical	Max	Unit
Analog input voltage	VAIN	V_{SS} – 0.3	—	V_{DD}	V
Analog input offset voltage	VAIO		—	40	mV
Analog Comparator initialization delay	t_{AINIT}		—	1	µs
Analog Comparator bandgap reference voltage	V_{BG}	1.208	1.218	1.228	V

A.10 FLASH Specifications

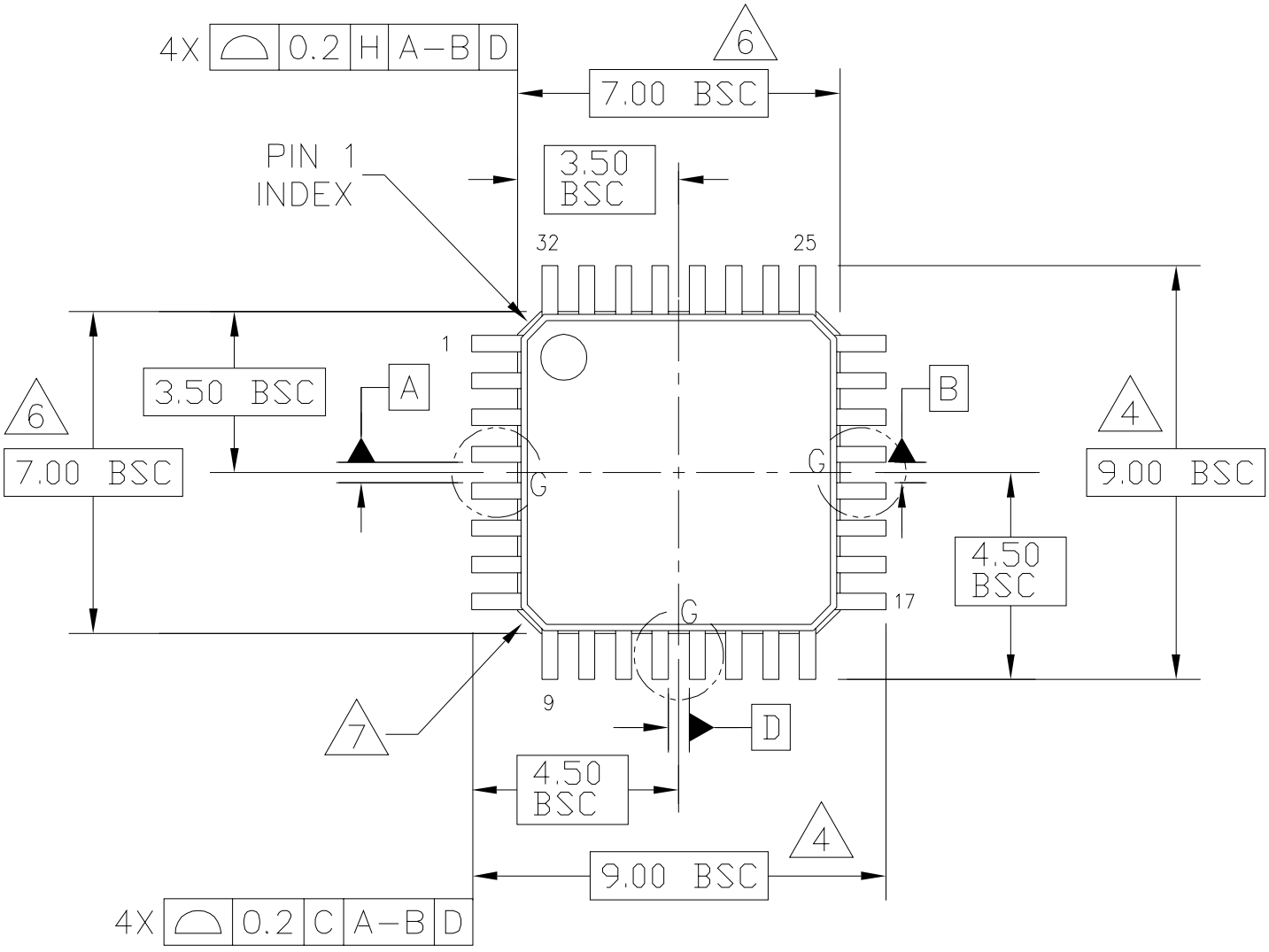
This section provides details about program/erase times and program-erase endurance for the FLASH memory.

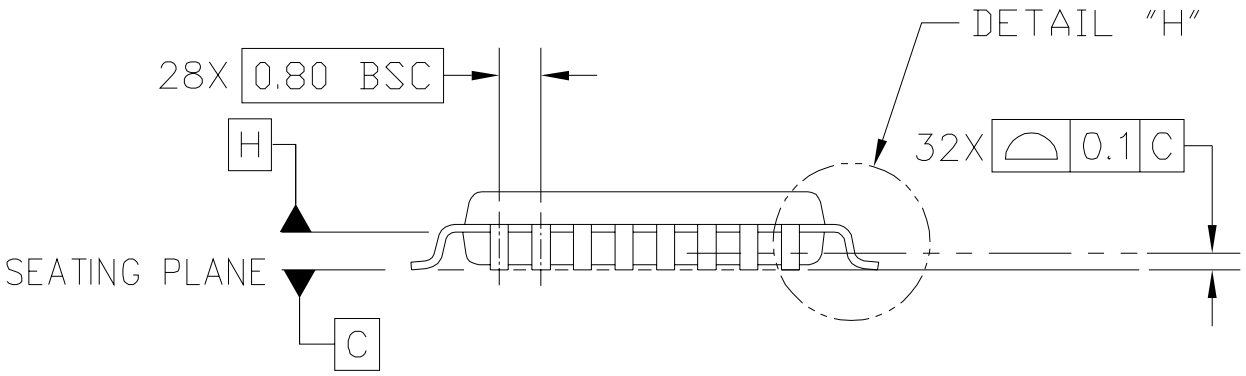
Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory chapter.

Table A-12. FLASH Characteristics

Characteristic	Symbol	Min	Typical	Max	Unit
Supply voltage for program/erase	$V_{prog/erase}$	2.05		3.6	V
Supply voltage for read operation $0 < f_{Bus} < 8$ MHz	V_{Read}	1.8		3.6	V
Internal FCLK frequency(1)	f_{FCLK}	150		200	kHz
Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	µs
Byte program time (random location)(2)	t_{prog}	9			t_{Fcyc}
Byte program time (burst mode)(2)	t_{Burst}	4			t_{Fcyc}
Page erase time(2)	t_{Page}	4000			t_{Fcyc}
Mass erase time(2)	t_{Mass}	20,000			t_{Fcyc}
Program/erase endurance(3) T_L to T_H = –40°C to + 85°C T = 25°C		10,000	 100,000	 —	cycles
Data retention(4)	t_{D_ret}	15	100	—	years

1. The frequency of this clock is controlled by a software setting.
2. These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.
3. **Typical endurance for FLASH** was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory.*
4. **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, *Typical Data Retention for Nonvolatile Memory.*





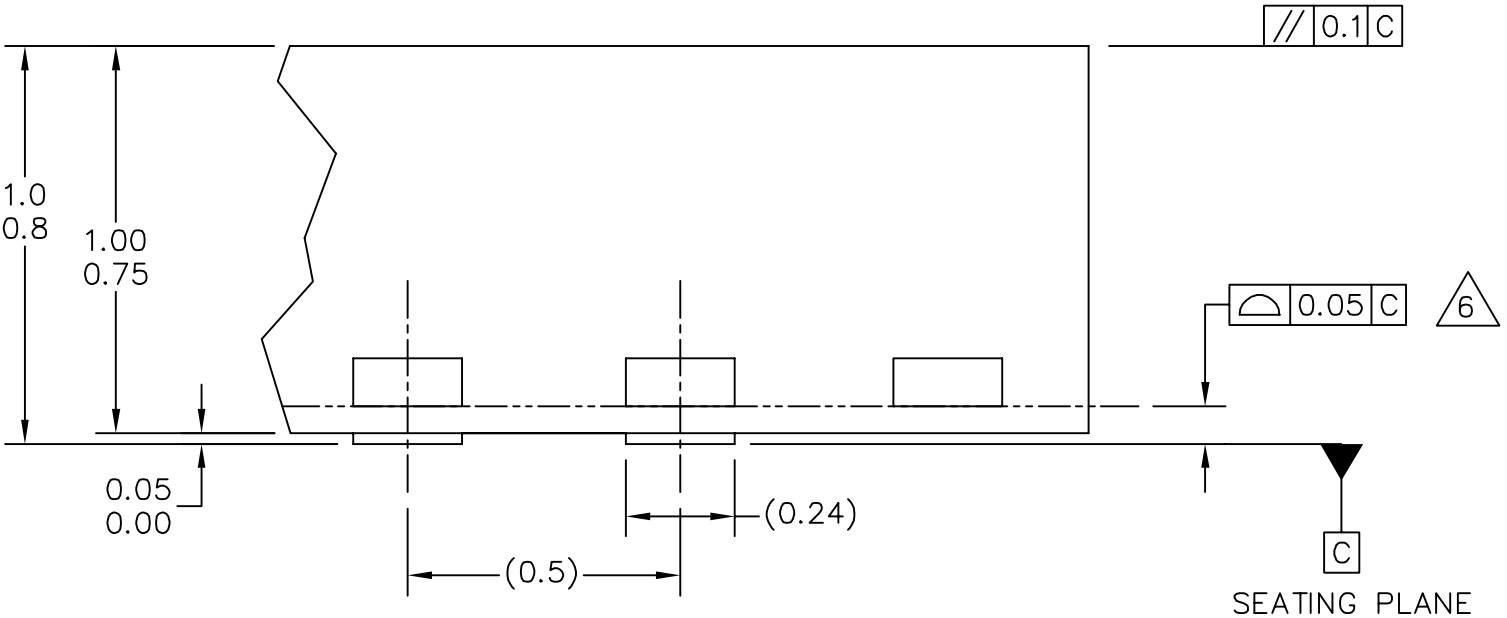
TITLE:

LOW PROFILE QUAD FLAT PACK (LQFP)
32 LEAD, 0.8 PITCH (7 X 7 X 1.4)

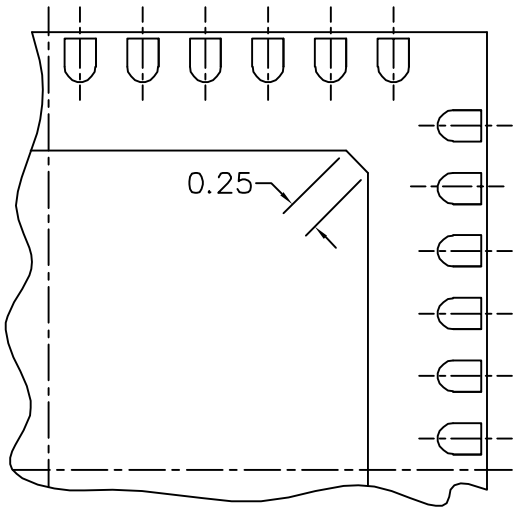
CASE NUMBER: 873A-04

STANDARD: JEDEC MS-026 BBA

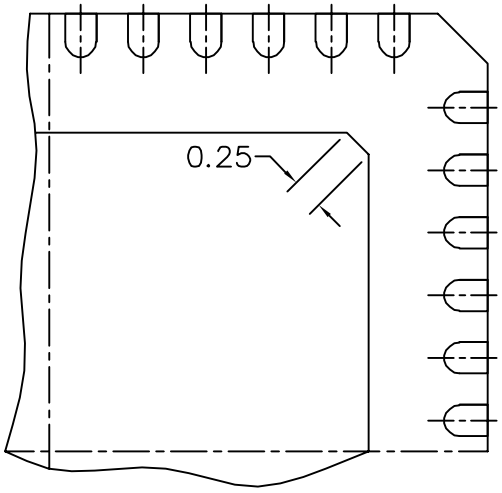
PACKAGE CODE: 6300



DETAIL G
VIEW ROTATED 90° CW



DETAIL M
PREFERED PIN 1 BACKSIDE IDENTIFIER



DETAIL M
PIN 1 BACKSIDE IDENTIFIER OPTION1

TITLE: THERMALLY ENHANCED QUAD FLAT NON-LEADED PACKAGE (QFN) 48 TERMINAL, 0.5 PITCH (7 X 7 X 1)

CASE NUMBER: 1314-03
STANDARD: JEDEC-MO-220 VKKD-2
PACKAGE CODE: 6152

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